

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S22	120	(crystalline near3 substrate) with light adj emitting	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/07 09:32
S23	45	S22 and buffer	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/07 09:32
S24	512	(crystalline near3 substrate) with buffer	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/07 09:34
S25	405	S24 and silicon	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/07 09:34
S26	330	S25 and nitride	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/07 09:34
S27	309	S26 and crystal\$3	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/07 09:34
S28	268	S27 and (epi\$6 epitaxial epitaxy) near3 (layer film)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/07 09:47
S29	268	S28 and layer	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/07 09:48
S30	268	S29 and substrate	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/07 09:48
S31	40	S30 and plasma	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/07 09:49

S32	249	S30 and thermal	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/07 09:49
S33	265	S30 and (thermal anneal\$3 heat\$3)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/07 09:51
S34	7	S33 and (nitrify nitrifying nitrification nitrided nitridation)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/07 10:14
S35	0	S33 and ((nitrify nitrifying nitrification nitrided nitridation) near3 plasma)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/07 10:20
S36	1049	((nitrify nitrifying nitrification nitrided nitridation) near3 plasma)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/07 09:53
S37	23078	((silicon monocrystal\$4 crystal\$3 'si') near3 substrate) with nitride	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/07 10:15
S38	2512	S37 and buffer near4 (layer film)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/07 10:17
S39	20	S37 and buffer near4 (double)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/07 10:19
S40	18	S37 and double near3 buffer	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/07 10:17
S41	27	S37 and multiple near3 buffer	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/07 10:18
S43	702	S37 and buffer near4 (first)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/07 10:19

S44	330	S37 and buffer near4 (second)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/07 10:19
S45	3	S44 and ((nitrify nitrifying nitrification nitrided nitridation) near3 plasma)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/07 10:25
S46	35	S44 and (nitrify nitrifying nitrification nitrided nitridation)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/07 10:26
S47	35	S46 and (nitrify nitrifying nitrification nitrided nitridation buffer layer first second subatrate)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/07 10:27
S48	23078	((silicon monocrystal\$4 crystal\$3 'si') near3 substrate) with nitride	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/07 15:36
S49	1	S48 and triple near3 buffer	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/07 15:36